## TGA2625-CP 10-11 GHz 20 W GaN Power Amplifier

#### **Product Description**

Qorvo's TGA2625-CP is a packaged high-power X-Band amplifier fabricated on Qorvo's QGaN25 0.25 um GaN on SiC process. Operating from 10 to 11 GHz, the TGA2625-CP achieves 42.5 dBm saturated output power, a power-added efficiency of > 40 %, and power gain of 28 dB.

The TGA2625-CP is packaged in a 10-lead 15x15 mm boltdown package with a Cu base for superior thermal management. It can support a range of bias voltages and performs well under CW and pulsed conditions. Both RF ports are internally DC blocked and matched to 50 ohms allowing for simple system integration.

The TGA2625-CP is ideally suited for both commercial and defense applications.

Lead free and RoHS compliant.

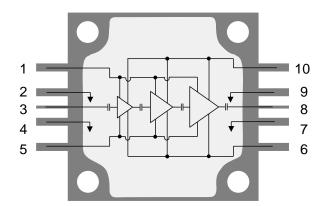
Evaluation Boards are available upon request.



#### **Product Features**

- Frequency Range: 10 11 GHz
- Pout: 42.5 dBm (at P<sub>IN</sub> = 15 dBm)
- PAE: > 40 %
- Power Gain: 28 dB (at P<sub>IN</sub> = 15 dBm)
- Bias: V\_D = 28 V, I\_{DQ} = 365 mA, V\_G = -2.6 V typical, pulsed (PW = 100  $\mu s,$  DC = 10 %)
- Package Dimensions: 15.2 x 15.2 x 3.5 mm
- Package base is pure Cu offering superior thermal management

#### **Functional Block Diagram**



#### **Applications**

- Radar
- Communications

#### **Ordering Information**

Part No.	Description		
TGA2625-CP	10-11 GHz 20 W GaN Power Amplifier		

### TGA2625-CP 10-11 GHz 20 W GaN Power Amplifier

#### **Absolute Maximum Ratings**

Parameter	Value / Range
Drain Voltage (V <sub>D</sub> )	40 V
Gate Voltage Range (V <sub>G</sub> )	-8 to 0 V
Drain Current (I <sub>D</sub> )	3 A
Gate Current (I <sub>G</sub> )	-6 to 14 <sup>(1)</sup> mA
Power Dissipation (PDISS), 85 °C	53 W
Input Power, CW, 50 Ω, (P <sub>IN</sub> )	21 dBm
Input Power, CW, VSWR 6:1, V <sub>D</sub> = 28 V, 85 °C, (P <sub>IN</sub> )	21 dBm
Mounting Temperature (30 Seconds)	260 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

(1) Max rating for IG is at Channel Temperature (TCH) of 200 °C.

#### **Recommended Operating Conditions**

Parameter	Value / Range
Drain Voltage (V <sub>D</sub> ) pulsed: PW = 100 $\mu$ s, DC = 10 %	28 V
Drain Current (I <sub>DQ</sub> )	365 mA
Drain Current Under RF Drive (I <sub>D_DRIVE</sub> )	See plots p. 6
Gate Voltage (V <sub>G</sub> )	−2.6 V (Typ.)
Gate Current Under RF Drive (Ig_DRIVE)	See plots p. 6
Temperature (T <sub>BASE</sub> )	-40 to 85 °C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

#### **Electrical Specifications**

Parameter	Min	Тур	Max	Units
Operational Frequency Range	10		11	GHz
Small Signal Gain		36		dB
Input Return Loss		13.5		dB
Output Return Loss		10		dB
Output Power (at P <sub>IN</sub> = 15 dBm)		42.5		dBm
Power Added Efficiency (at P <sub>IN</sub> = 15 dBm)		40		%
Power Gain (at P <sub>IN</sub> = 15 dBm)		28		dB
Output Power Temperature Coefficient Pulsed (25 °C to 85 °C only) CW		-0.003 -0.01		dBm/°C
Recommended Operating Voltage	25	28	32	V

Test conditions unless otherwise noted: 25 °C,  $V_D = 28$  V (PW = 100  $\mu$ s, DC = 10 %),  $I_{DQ} = 365$  mA,  $V_G = -2.6$  V typical.

# QOrvo

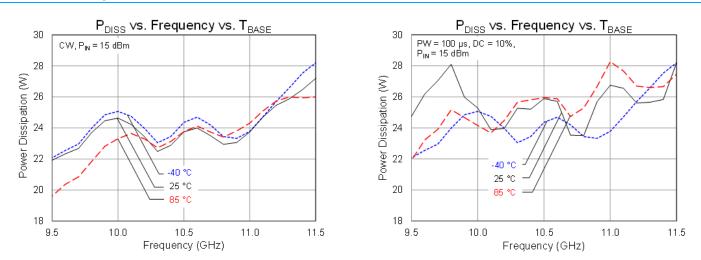
#### Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup>	CW, $V_D = 28 V$ , $I_{DQ} = 365 mA$ ,	2.25	°C/W
Channel Temperature (T <sub>CH</sub> ) (under RF drive)	T <sub>BASE</sub> = 85°C, Freq = 10.5 GHz, P <sub>IN</sub> = 15 dBm, P <sub>OUT</sub> = 42.4 dBm P <sub>DISS</sub> =24 W, I <sub>D_Drive</sub> = 1.46 A	139	°C
Thermal Resistance ( $\theta_{JC}$ ) <sup>(1)</sup>	$V_D = 28 V, I_{DQ} = 365 mA,$	1.57	°C/W
Channel Temperature (T <sub>CH</sub> ) (under RF drive)	$\label{eq:powerserv} \begin{array}{ c c c c c c } \hline (Pulsed: PW = 100 \ \mu s, \ DC = 10 \ \%), \\ \hline T_{BASE} = 85^{\circ}C, \ Freq = 10.5 \ GHz, \ P_{IN} = 15 \ dBm, \\ \hline P_{OUT} = 42.8 \ dBm, \ P_{DISS} = 26 \ W, \ I_{D\_Drive} = 1.61 \ A \end{array}$	126	°C

Notes:

1. Thermal resistance measured to back of package.

2. Refer to the following document: GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates

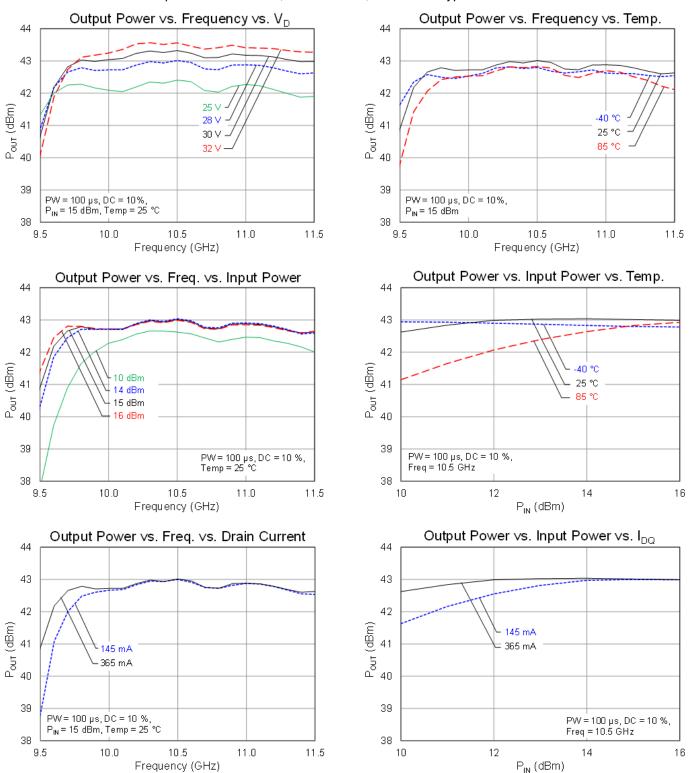


#### **Power Dissipation**

## **TGA2625-CP** 10 – 11 GHz 20 W GaN Power Amplifier

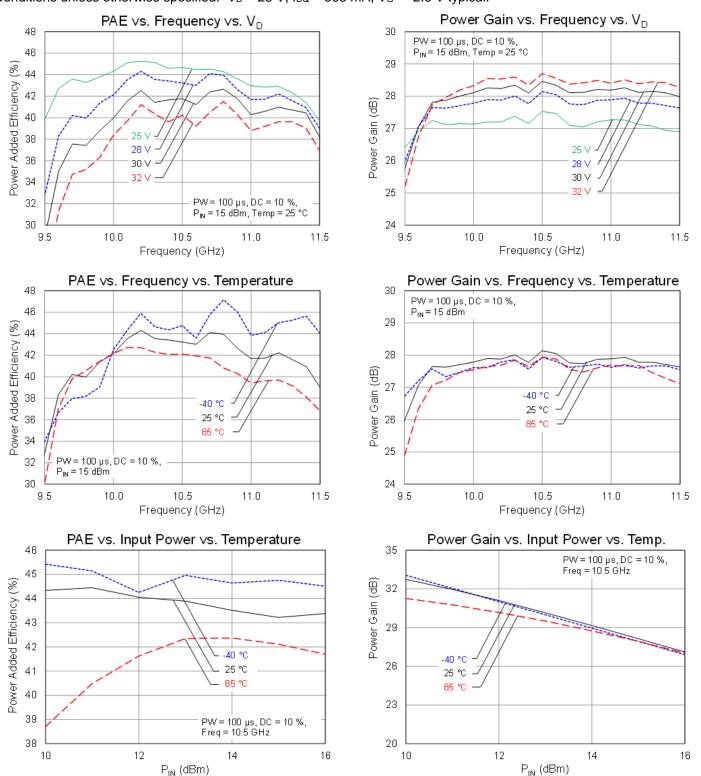
#### **Typical Performance – Large Signal**

Conditions unless otherwise specified: V<sub>D</sub> = 28 V, I<sub>DQ</sub> = 365 mA, V<sub>G</sub> = -2.6 V typical.



## TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

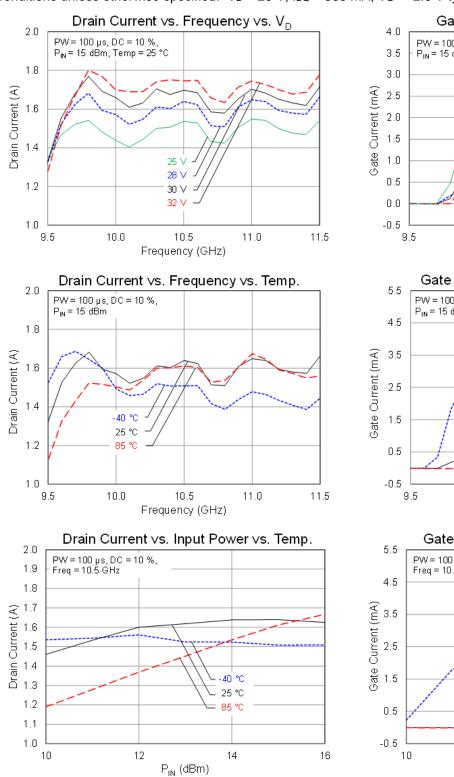
#### Typical Performance – Large Signal (Pulsed)

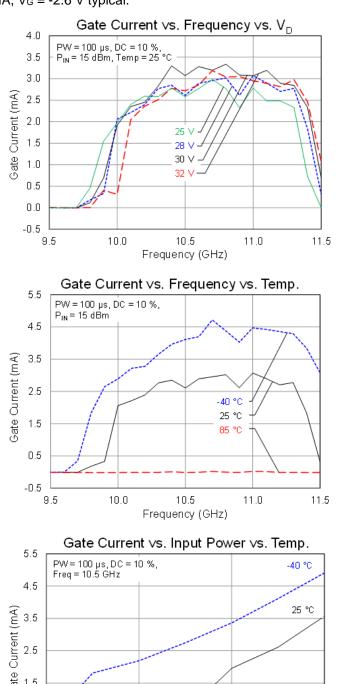


## **TGA2625-CP** 10 – 11 GHz 20 W GaN Power Amplifier

#### Typical Performance – Large Signal (Pulsed)

Conditions unless otherwise specified:  $V_D = 28 \text{ V}$ ,  $I_{DQ} = 365 \text{ mA}$ ,  $V_G = -2.6 \text{ V}$  typical.





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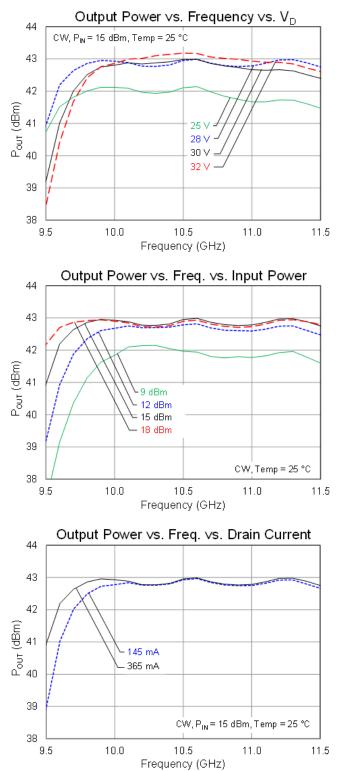
P<sub>IN</sub> (dBm)

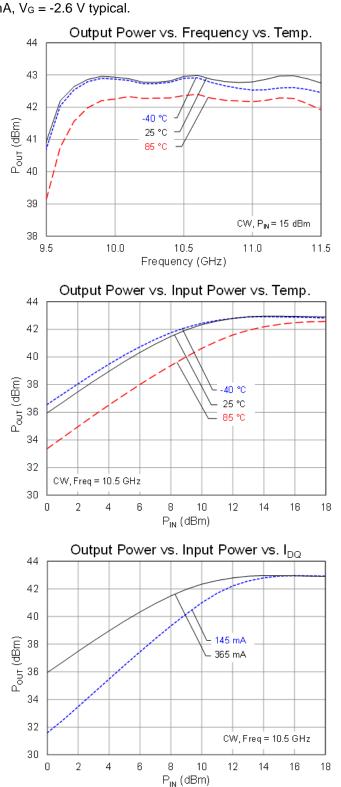
85 °C

16

14

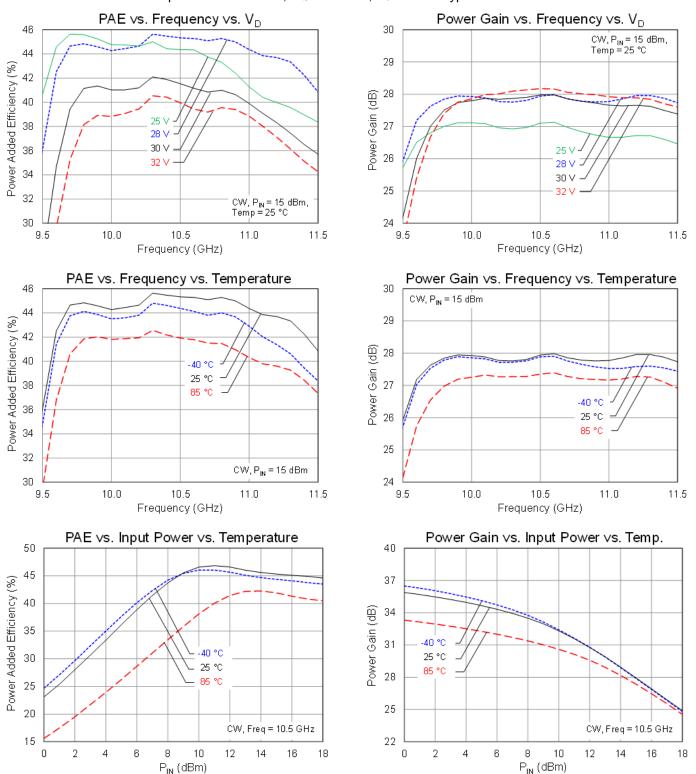
#### Performance Plots – Large Signal (CW)





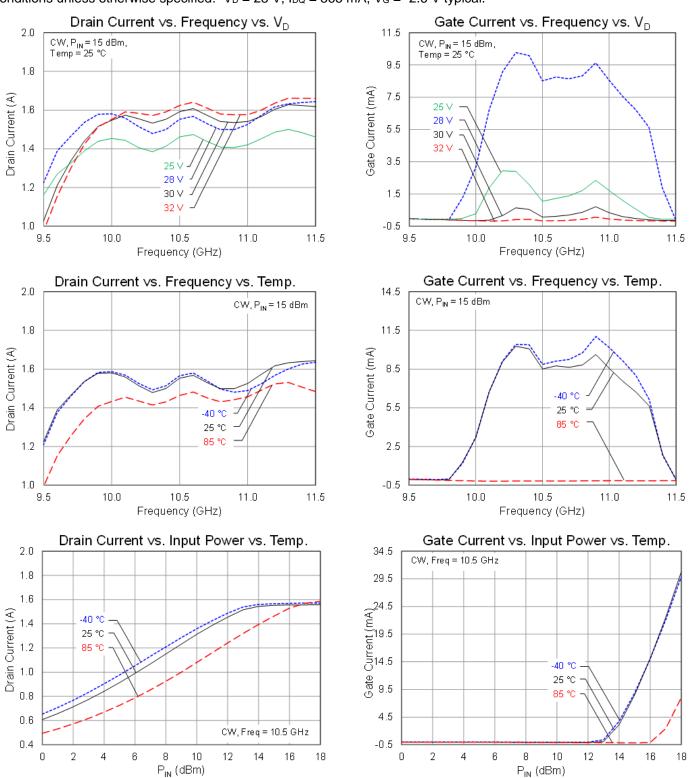
## TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

#### Performance Plots – Large Signal (CW)



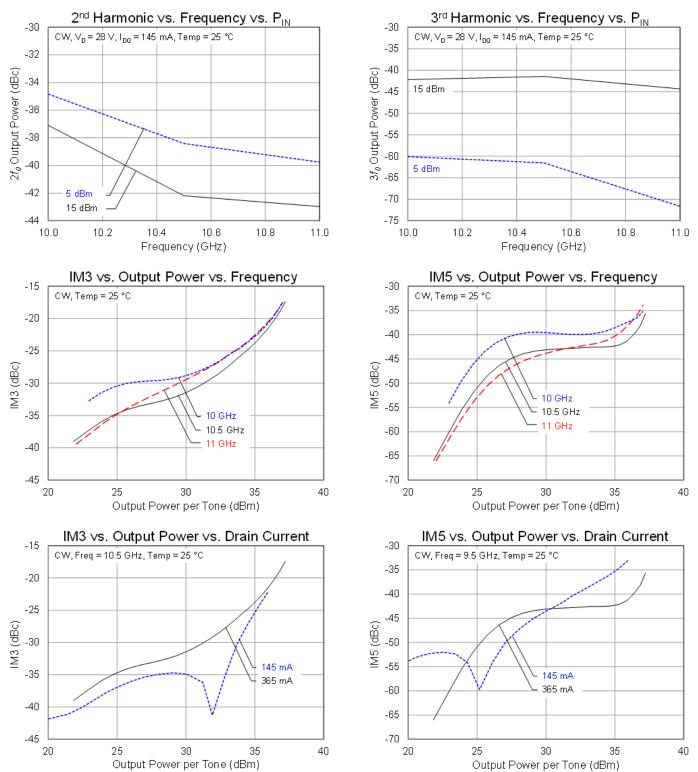
## TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

#### Performance Plots – Large Signal (CW)

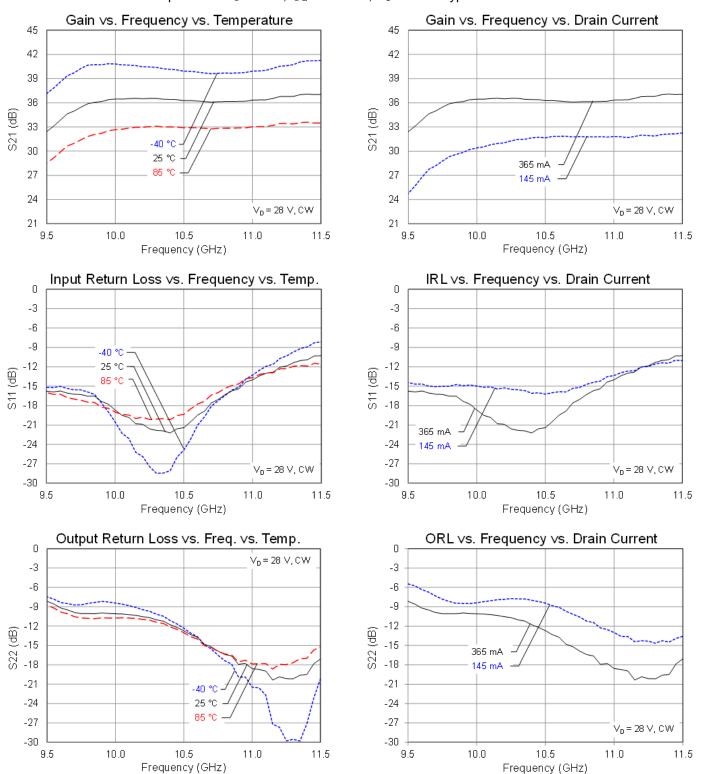


## **TGA2625-CP** 10 – 11 GHz 20 W GaN Power Amplifier

#### **Typical Performance – Linearity**

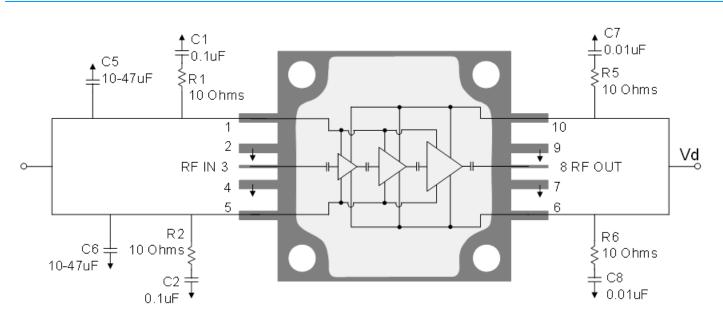


#### **Typical Performance – Small Signal**



## TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

#### **Applications Information and Pin Layout**



#### **Bias Up Procedure**

- 1. Set  $I_D$  limit to 3 A,  $I_G$  limit to 14 mA
- 2. Apply –5 V to  $V_{\rm G}$
- 3. Apply +28 V to  $V_{\text{D}};$  ensure  $I_{\text{DQ}}$  is approx. 0 mA
- 4. Adjust V<sub>G</sub> until  $I_{DQ}$  = 365 mA (V<sub>G</sub> ~ -2.6 V Typ.).
- 5. Turn on RF supply

#### **Bias Down Procedure**

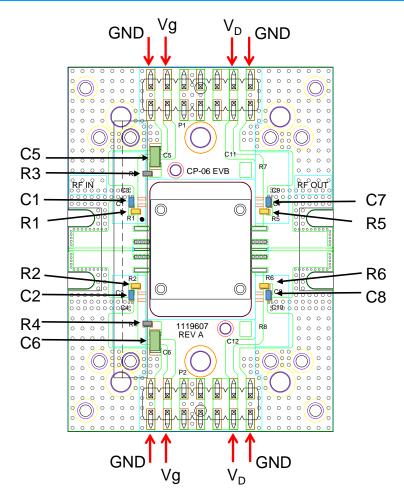
- 1. Turn off RF supply
- 2. Reduce V<sub>G</sub> to -5 V; ensure I<sub>DQ</sub> is approx. 0 mA
- 3. Set  $V_{\text{D}}$  to 0 V
- 4. Turn off  $V_{\mathsf{D}}$  supply
- 5. Turn off  $V_G$  supply

#### **Pin Description**

Pad No.	Symbol	Description
1, 5	V <sub>G</sub>	Gate Voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
3	RFIN	Output; matched to 50 Ω; DC blocked
2, 4, 7, 9	GND	Must be grounded on the PCB.
6, 10	VD	Drain voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
8	RFout	Input; matched to 50 $\Omega$ ; DC blocked

### TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

#### **Evaluation Board (EVB)**



#### NOTES:

#### **Bill of Materials**

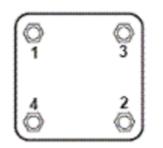
Reference Des.	Value	Description	Manuf.	Part Number
C1, C2	0.1 uF	Cap, 0402, 50 V, 10%, X7R	Various	
C5, C6	10-47 uF	Cap, 1206, 50 V, 20%, X5R (10v is OK)	Various	
C7, C8	0.01 uF	Cap, 0402, 50V, 10%, X7R	Various	
R1, R2, R5, R6	10 Ohms	Res, 0402, 50V, 5%	Various	
R3, R4	0 Ohms	Res, 0402, jumper required for the above EVB design	Various	

<sup>(1)</sup> Both Top and Bottom Vd and Vg must be biased.

### **TGA2625-CP** 10 – 11 GHz 20 W GaN Power Amplifier

#### **Assembly Notes**

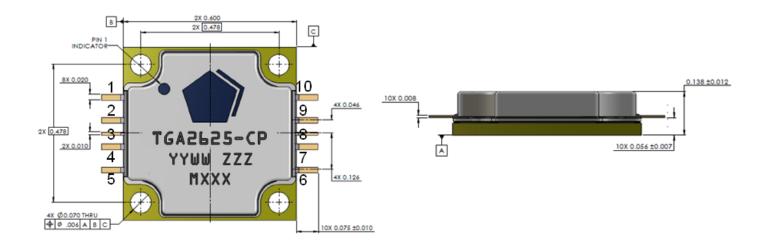
- 1. Carefully clean the PC board and package leads with alcohol. Allow it to dry fully.
- 2. To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom of the PCB and apply thermal compound (Arctic Silver 5 recommended) or 4 mil indium shim between the heat sink and the package.
- 3. (The following is for <u>information only</u>. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:



 Apply no-flux solder to each pin of the TGA2625-CP. The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.

### TGA2625-CP 10-11 GHz 20 W GaN Power Amplifier

#### **Mechanical Information**



Units: inches Tolerances: unless specified  $x.xx = \pm 0.01$   $x.xxx = \pm 0.005$ Materials: Base: Copper Lid: Plastic All metalized features are gold plated Part is epoxy sealed Marking: 2625: Part number YY: Part Assembly year WW: Part Assembly week ZZZ: Serial Number MXXX: Batch ID

### TGA2625-CP 10 – 11 GHz 20 W GaN Power Amplifier

#### Handling Precautions

Parameter	Rating	Standard	
ESD-Human Body Model (HBM)	1B	ESDA/JEDEC JS-001-2014	Caution!
ESD-Charged Device Model (CDM)	C0B	ESDA/JEDEC JS-002-2014	ESD-Sensitive Device
MSL-Moisture Sensitivity Level	N/A		

#### Solderability

The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. Soldering of the component leads is compatible with the latest version of J-STD-020, lead-free solder, 260 °C. The use of no-clean solder to avoid washing after soldering is recommended.

#### **RoHS Compliance**

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>0<sub>2</sub>) Free
- PFOS Free
- SVHC Free

#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations:

- Web: <u>www.qorvo.com</u>
- Tel: 1-844-890-8163
- Email: customer.support@gorvo.com

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